



Deterministic and Scalable Growth of Electrically Self-Contacted 2D Materials-Based Devices

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ONQPI 2D Materials-Based Devices

Mechanical Exfoliation







http://www.planarmaterials.com/store/p144/Hi gh_mobility_graphene_heterostructures.html



Nanocarbon group, DTU Nanotech, Technical University of Denmark

Challenges

- Variability
- Reproducibility
- Contacting
- Scalability





ONQPI 2D Materials-Based Devices



Scientific reports 3 (2013): 1866.



Reverse the process

Start with device structure



Grow material





1DG



M. H. D. Guimaraes, et al, ACS Nano 10, 6392 (2016)



As-grown 2D Devices

Deterministic

NQPI

- Scalable
- Compatible with existing silicon processing
- Provides concurrent, asgrown, electrical contacts
- Heterostructures
- Direct on-chip optics?
- Doping?
- Complex geometries?







ONQPI

MoS₂ on Mo 4-probe

UNIVERSITY



DOI: 10.1002/admi.201600599 or arXiv:1611.03887

ONQPI Continuous mono MoS₂ between the patterns



DOI: 10.1002/admi.201600599 or arXiv:1611.03887

ONQPI

Heterostructure Growth

UNIVERSITY



MoS₂/WS₂ vertical heterostructures grown on tungsten wires

Khadka S., et al. Advanced Materials Interfaces (2016)**DOI:**10.1002/admi.201600599 or arXiv:1611.03887



Heterostructure Growth



Combinations of metal pattern and oxide precursor may lead to straightforward production of complex device structures

Characterization of As-grown Device

a) Raman Mapping

Khadka S., et al. Advanced Materials Interfaces (2016) DOI: 10.1002/admi.201600599 arXiv:1611.03887 or

QPI

ONQPI Experimental Set Up for Electrical Measurements

a.

3D scehmatic of the asgrown MoS₂ based MSM PD

b. **Cross-sectional representation of** PD with the electrical contacts used for the measurements of **Photocurrent and Photo** responsivity 532 nm Mo Mo (D) **(S)** SiO₂ Si V_{DS} V_{GS}

ONOPI Photocurrent and Photoresponsivity

Photocurrent = *I*_{*Illuminated*} – *I*_{*dark*}(A)

Photoresponsivity (R) = $\frac{Photocurrent}{Incident Power}$ (A/W)

Photocurrent Dynamics

JQPI

ONQPI Bias dependent Spatial Photocurrent

Optical Image

Photocurrent Mapping at V_{DS} =0V

Line profile of Photocurrent across green line at $V_{DS}=\pm 0.5$, 0V

ONQPI Comparison with previously reported MoS₂ PDs.

Ref: Buscema, Michele, et al. Chemical Society Reviews 44.11 (2015): 3691-3718.

ONQPI Summary of the Presentation

ONQPI

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